

## Asymmetrical TVS Diode

The ASM712 is designed for asymmetrical (12V to -7V) protection in multi-point data transmission application, The ASM712 replace four discrete components by inte-grating two 12V and two 7V TVS diodes in a single pack-age. The ASM712 complies with the IEC 61000-4-2 (ESD) standard with  $\pm 15\text{kV}$  air and  $\pm 8\text{kV}$  contact dis-charge. It is assembled into a lead-free SOT-23 package. It is designed to protect components which are connected to data and transmission lines from voltage surges.

### Features

- 400W peak pulse power (8/20us)
- Ultra low leakage : nA level
- Operating voltage : 7V or 12V
- Low clamping voltage
- Complies with following standards :
  - IEC 61000-4-2 (ESD) immunity test  
Air discharge :  $\pm 30\text{kV}$ , Contact discharge :  $\pm 30\text{kV}$
  - IEC61000-4-4 (EFT) 40A (5/50ns)
  - IEC61000-4-5 (Lightning) 17A(8/20us)
- RoHS Compliant

### Mechanical Data

- Package : SOT-23
- Case Material : "Green" Molding Compound.
- Lead Finish : Matte Tin
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity : Level 3 per J-STD-020
- Terminal Connections : See Diagram Below
- Marking Information : See Below

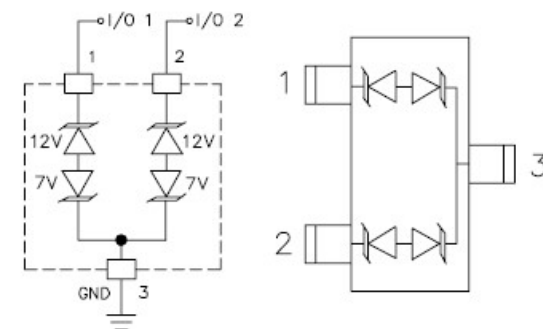
### Applications

- Wireless System
- Networks
- Portable Instrumentation
- RS485 Ports

### Marking



B712 = Device Marking Code



Circuit and Pin Schematic

### Absolute Maximum Ratings (Ta= 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20us)	Ppk	400	W
Peak Pulse Current (8/20us)	Ipp	17	A
ESD per IEC 61000-4-2 (Air)	V <sub>ESD</sub>	$\pm 30$	kV
ESD per IEC 61000-4-2 (Contact)		$\pm 30$	
Operating Junction Temperature Range	T <sub>J</sub>	-55 to +125	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C

SOT-23		
DIM	Unit : mm	
	MIN	MAX
A	1.15	1.50
B	2.70	3.10
b	0.35	0.55
C	-	1.30
C1	0.90	1.20
c	0.05	0.20
E	1.70	2.10
E1	0.85	1.05
K	0	0.10
L	2.20	2.70
L1	0.45	0.65
M	0.20	-
P	7°	

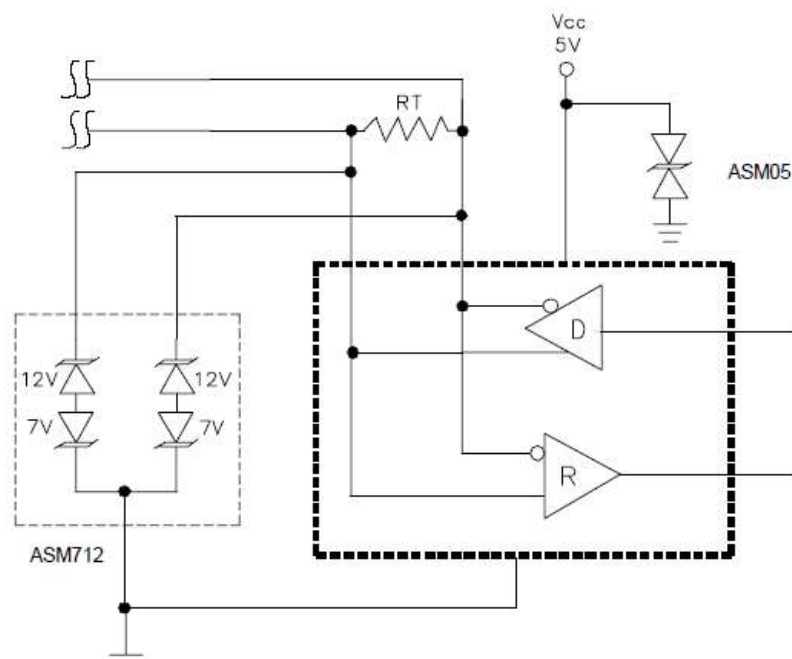
**Electrical Characteristics (Ta= 25°C unless otherwise specified)**

Characteristic	Symbol	7V TVS (Pin 3 to 1 and 3 to 2)			Unit	Test Condition
		Min.	Typ.	Max.		
Reverse Working Voltage	$V_{RWM}$	-	-	7.0	V	
Breakdown Voltage	$V_{BR}$	7.5	-	-	V	$I_T = 1mA$ ,
Reverse Leakage Current	$I_R$	-	-	2.0	$\mu A$	$V_R = V_{RWM}$
Clamping Voltage	$V_C$	-	-	10	V	$I_{PP} = 5A(8 \times 20\mu s \text{ pulse})$
		-	-	12	V	$I_{PP} = 17A(8 \times 20\mu s \text{ pulse})$
Junction Capacitance	$C_J$	-	-	75	pF	$f = 1MHz, V_R = 0V$
		-	45	-	pF	$f = 1MHz, V_R = V_{RWM}$

Characteristic	Symbol	12V TVS (Pin 1 to 3 and 2 to 3)			Unit	Test Condition
		Min.	Typ.	Max.		
Reverse Working Voltage	$V_{RWM}$	-	-	12.0	V	
Breakdown Voltage	$V_{BR}$	13.3	-	-	V	$I_T = 1mA$ ,
Reverse Leakage Current	$I_R$	-	-	0.05	$\mu A$	$V_R = V_{RWM}$
Clamping Voltage	$V_C$	-	-	20	V	$I_{PP} = 5A(8 \times 20\mu s \text{ pulse})$
		-	-	26	V	$I_{PP} = 17A(8 \times 20\mu s \text{ pulse})$
Junction Capacitance	$C_J$	-	-	75	pF	$f = 1MHz, V_R = 0V$
		-	45	-	pF	$f = 1MHz, V_R = V_{RWM}$

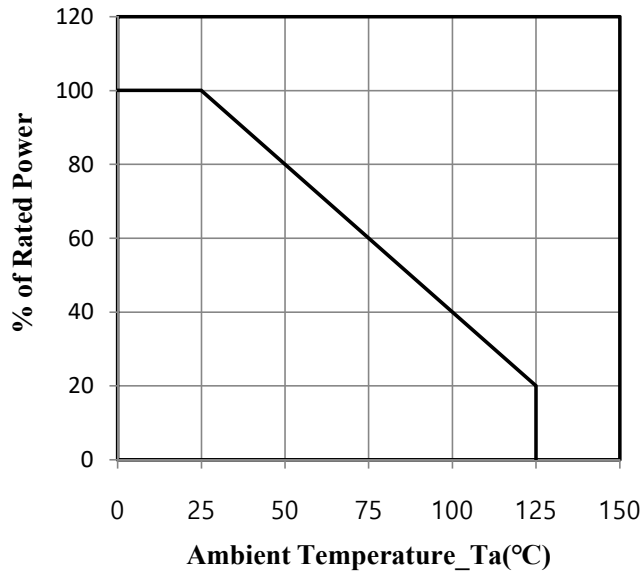
**ASM712 on RS-485 Data Lines Application**

EIA RS-485 specifies a  $\pm 7V$  ground difference between devices on the bus. This permits the bus voltage to range from +12V (5V + 7V) to -7V (0 - 7V). The ASM712 is designed to protect two RS-485 data lines in extended common mode applications. The ASM712 may be used to protect devices from transient voltages resulting from ESD, EFT, and lightning. The device is designed with asymmetrical operating voltages for optimum protection. The TVS diodes at pins 1 and 2 have a working voltage of 12volts. These pins are connected to the differential data line pairs. The TVS diodes at pin 3 have a working voltage of 7volts. Pin 3 is connected to ground. The internal TVS diodes of the ASM712 will protect the transceiver input from positive transient voltage spikes greater than 12V and negative spikes greater than 7V.

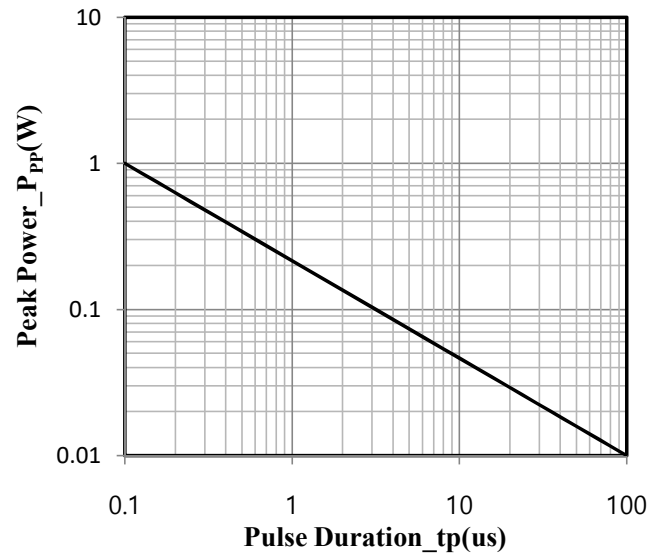


Ratings and Characteristics Curves ( $T_a=25^{\circ}\text{C}$  unless otherwise noted)

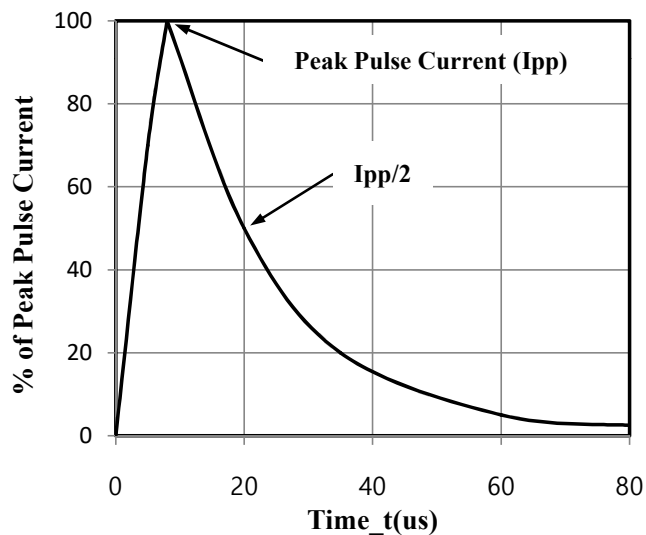
**Fig.1 Power Derating Curve**



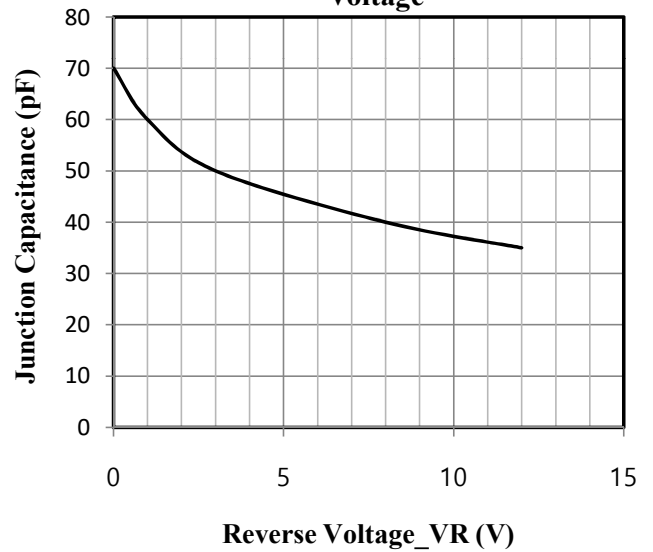
**Fig.2 Peak Pulse Power vs. Pulse Time**



**Fig.3 8 × 20us Pulse Waveform**



**Fig.4 Junction Capacitance vs. Reverse Voltage**



**Fig.5 Clamping Voltage vs. Peak Pulse Current ( $t_p=8/20\mu\text{s}$ )**

